

Modeling Electrical Conductivity in Metallic Crystals using a Lattice-Site Model

Predictive Science and Engineering Design Cluster 2011

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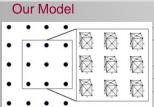
Motivation and **Applications**

Electrical Conductivity in Metal Organic Frameworks

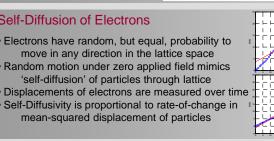
- Metal Organic Frameworks are pourous crystalline materials
- □ MOFs are well suited to adsorption and separation applications
- Electrically conductive MOFs can be used as novel sensing devices

Forming

- Electric current changes mechanical properties of metals
- Electrical effect occurs in addition to thermal effects (resistive heating)
- Effect is linked to resistivity and conductivity of material



- Each site in lattice corresponds to unit cell of crystal · Periodic boundary conditions allow a finite lattice
- size to represent infinitely-large material body
- Populate lattice with specified density of electrons
- · Use random and field-driven motion to propel electrons
- Compute electron flux and conductivity over time

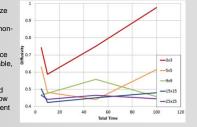


 $\sigma =$

 $k_{\rm n}T$

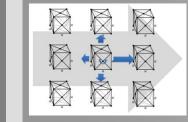
[Left-top]: Small lattice size (3x3 particles) shows unstable self-diffusivity (nonlinear) [Left-bottom]: Larger lattice (9x9 particles) shows stable, linear self-diffusivity

> [Right]: Large lattices and long simulation times show most stable and convergent solution for diffusivity



Conduction of Electrons under Applied Electric Field (with Random Material Defects)

 $\overline{BT}czF\mathbf{E}$



h

(4%

(50

Objectives

Develop a simple and computationally inexpensive

· Use model to bridge gap between atomistic and

continuum scale models

model that can simulate movement of electrons

material defects and observe their implications

Random Walk and Self-Diffusion of Electrons

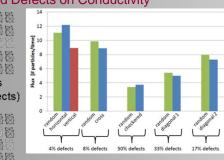
· Design the framework so users can easily implement

 Apply electric field by increasing probability of electron motion in a specified direction (ie. 'right') · At defect sites, electrons regain random walk motion Measure flux of electrons through wall of lattice (wall is perpendicular to flow of electrons) •Flux of electrons is proportional to conductivity $N_{\mu}e^{2}D$

Influence of Random vs. Ordered Defects on Conductivity

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heckered (%) (%) (%) (%) (%) (%) (%) (%) (%) (%)	정 정 정 정 정 정 성 성 성 (33% defects)	diagonal 2 (17% defect



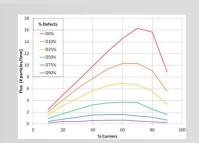
[Right]: Various configurations of ordered defects and their corresponding defect density

[Top]: When comparing random and ordered defects, certain configurations of ordered defects (especially at low densities) can greatly influence overall conductivity

[Right]: Increasing % charge carriers (up to 50%) increases conductivity

 Increasing % defects decreases conductivity

 Maximum conductivity occurs between 50-75% charge carrier density



Conclusions

• Our model provides a computationally inexpensive means of determining trends between charge carrier density, defect density, and defect structure in lattices • Due to the nonlinearities and interactions in the model, the model is well suited for parameter optimization

Future Work

- Build material complexity into model framework: -Alloying, defect-interaction, electron occupancy -Lattice packing structure
- Further investigate structures of ordered defects: -Construct 'grain boundaries' in lattice model
- Apply model for design and optimization of conductive and metallic materials in electronic applications